

μPD5756T6N

SiGe BiCMOS Integrated Circuit Wide Band LNA IC with Through Function

Data Sheet

R09DS0026EJ0100
 Rev.1.00
 Oct 04, 2011

DESCRIPTION

The μPD5756T6N is a low noise wideband amplifier IC with the through function mainly designed for the digital TV application. This IC exhibits low noise figure and low distortion characteristics.
 This IC is manufactured using our latest SiGe BiCMOS process that shows superior high frequency characteristics.

FEATURES

- Low voltage operation : $V_{CC} = 3.1$ to 3.5 V (3.3 V TYP.)
- Low current consumption : $I_{CC1} = 25$ mA TYP. @ $V_{CC} = 3.3$ V (LNA-mode)
 : $I_{CC2} = 1$ μA MAX. @ $V_{CC} = 3.3$ V (Bypass-mode)
- Operation frequency : $f = 40$ to $1\,000$ MHz
- Low noise : $NF = 3.2$ dB TYP. @ $f = 1\,000$ MHz (LNA-mode)
- Low distortion : $IIP_3 = +9$ dBm TYP. @ $f_1 = 500$ MHz, $f_2 = 505$ MHz (LNA-mode)
- Low insertion loss : $L_{ins} = 1.7$ dB TYP. @ $f = 1\,000$ MHz (Bypass-mode)
- High-density surface mounting : 6-pin plastic TSON (T6N) package ($1.5 \times 1.5 \times 0.37$ mm)

APPLICATIONS

- Low noise amplifier for the digital TV system, etc.

ORDERING INFORMATION

Part Number	Order Number	Package	Marking	Supplying Form
μPD5756T6N-E2	μPD5756T6N-E2-A	6-pin plastic TSON (T6N) (Pb-Free)	C4C	• Embossed tape 8 mm wide • Pin 1, 6 face the perforation side of the tape • Qty 3 kpcs/reel

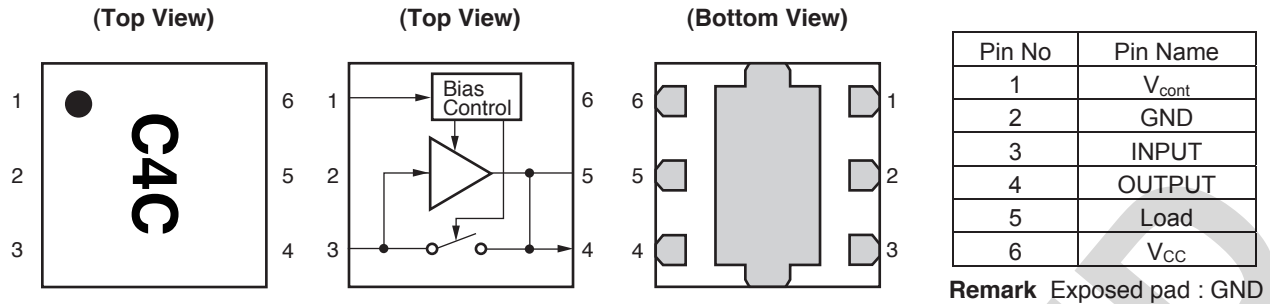
Remark To order evaluation samples, please contact your nearby sales office.

Part number for sample order: μPD5756T6N-A

CAUTION

Observe precautions when handling because these devices are sensitive to electrostatic discharge.

PIN CONNECTIONS, MARKING AND INTERNAL BLOCK DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Conditions	Ratings	Unit
Supply Voltage	V_{CC}	$T_A = +25^{\circ}\text{C}$	4.0	V
Mode Control Voltage	V_{cont}	$T_A = +25^{\circ}\text{C}$	4.0	V
Total Power Dissipation	P_{tot}	$T_A = +85^{\circ}\text{C}$ Note	300	mW
Operating Ambient Temperature	T_A		-40 to +85	$^{\circ}\text{C}$
Storage Temperature	T_{stg}		-55 to +150	$^{\circ}\text{C}$
Input Power	P_{in}	$T_A = +25^{\circ}\text{C}$, $Z_S = Z_L = 75\ \Omega$	+15	dBm

Note: Mounted on double-sided copper-clad 50 × 50 × 1.6 mm epoxy glass PWB

RECOMMENDED OPERATING RANGE

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Supply Voltage	V_{CC}	3.1	3.3	3.5	V
Mode Control Voltage (H)	$V_{cont(H)}$	1.0	—	V_{CC}	V
Mode Control Voltage (L)	$V_{cont(L)}$	-0.1	—	0.4	V
Operating Frequency	f	40	—	1 000	MHz
Operating Ambient Temperature	T_A	-40	+25	+85	$^{\circ}\text{C}$
Input Power (LNA-mode) Note	P_{in}	—	—	0	dBm
Input Power (Bypass-mode) Note	P_{in}	—	—	+10	dBm

Note: $T_A = +25^{\circ}\text{C}$, $Z_S = Z_L = 75\ \Omega$

ELECTRICAL CHARACTERISTICS 1 (DC Characteristics)
 ($T_A = +25^{\circ}\text{C}$, $V_{CC} = 3.3\text{ V}$, unless otherwise specified)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Circuit Current 1	I_{CC1}	$V_{cont} = 3.3\text{ V}$, No Signal (LNA-mode)	16	25	34	mA
Circuit Current 2	I_{CC2}	$V_{cont} = 0\text{ V}$, No Signal (Bypass-mode)	—	0.01	1	μA
Mode Control Current 1	I_{cont1}	$V_{cont} = 3.3\text{ V}$, No Signal (LNA-mode)	—	50	100	μA
Mode Control Current 2	I_{cont2}	$V_{cont} = 0\text{ V}$, No Signal (Bypass-mode)	—	0.01	1	μA

ELECTRICAL CHARACTERISTICS 2 (LNA-mode)**($T_A = +25^\circ\text{C}$, $V_{CC} = V_{cont} = 3.3\text{ V}$, $Z_S = Z_L = 75\ \Omega$, unless otherwise specified)**

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Power Gain 1	G_{P1}	$f = 40\text{ MHz}$, $P_{in} = -20\text{ dBm}$	10.5	13	15.5	dB
Power Gain 2	G_{P2}	$f = 1\ 000\text{ MHz}$, $P_{in} = -20\text{ dBm}$	10.5	13	15.5	dB
Noise Figure 1	NF1	$f = 40\text{ MHz}$, $Z_S = Z_L = 50\ \Omega$, excluded PCB and connector losses Note	–	3.2	4.2	dB
Noise Figure 2	NF2	$f = 1\ 000\text{ MHz}$, $Z_S = Z_L = 50\ \Omega$, excluded PCB and connector losses Note	–	3.2	4.2	dB
Input Return Loss 1	RL_{in1}	$f = 40\text{ MHz}$, $P_{in} = -20\text{ dBm}$	7	9	–	dB
Input Return Loss 2	RL_{in2}	$f = 1\ 000\text{ MHz}$, $P_{in} = -20\text{ dBm}$	7	10	–	dB
Output Return Loss 1	RL_{out1}	$f = 40\text{ MHz}$, $P_{in} = -20\text{ dBm}$	7	10	–	dB
Output Return Loss 2	RL_{out2}	$f = 1\ 000\text{ MHz}$, $P_{in} = -20\text{ dBm}$	7	12	–	dB
Input 3rd Order Intercept Point	IIP_3	$f_1 = 500\text{ MHz}$, $f_2 = 505\text{ MHz}$, $P_{in} = -20\text{ dBm}$	+5	+9	–	dBm

Note: Input PCB and connector losses : 0.03 dB (at 40 MHz), 0.10 dB (at 1 000 MHz)

ELECTRICAL CHARACTERISTICS 3 (Bypass-mode)**($T_A = +25^\circ\text{C}$, $V_{CC} = 3.3\text{ V}$, $V_{cont} = 0\text{ V}$, $Z_S = Z_L = 75\ \Omega$, unless otherwise specified)**

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Insertion Loss 1	L_{ins1}	$f = 40\text{ MHz}$, $P_{in} = -10\text{ dBm}$, excluded PCB and connector losses Note	–	0.5	1.5	dB
Insertion Loss 2	L_{ins2}	$f = 1\ 000\text{ MHz}$, $P_{in} = -10\text{ dBm}$, excluded PCB and connector losses Note	–	1.7	2.5	dB
Input Return Loss 1	RL_{in1}	$f = 40\text{ MHz}$, $P_{in} = -10\text{ dBm}$	10	26	–	dB
Input Return Loss 2	RL_{in2}	$f = 1\ 000\text{ MHz}$, $P_{in} = -10\text{ dBm}$	7	8	–	dB
Output Return Loss 1	RL_{out1}	$f = 40\text{ MHz}$, $P_{in} = -10\text{ dBm}$	10	25	–	dB
Output Return Loss 2	RL_{out2}	$f = 1\ 000\text{ MHz}$, $P_{in} = -10\text{ dBm}$	7	8	–	dB
Input 3rd Order Intercept Point	IIP_3	$f_1 = 500\text{ MHz}$, $f_2 = 505\text{ MHz}$, $P_{in} = -5\text{ dBm}$	+20	+29	–	dBm

Note: Input-output PCB and connector losses : 0.06 dB (at 40 MHz), 0.20 dB (at 1 000 MHz)

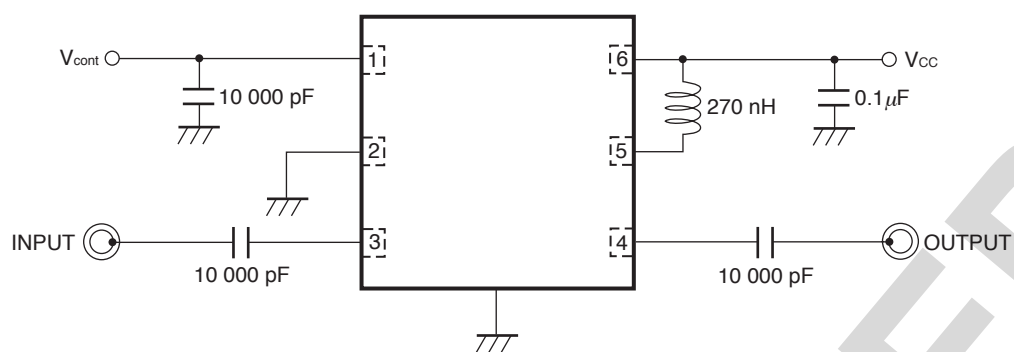
STANDARD CHARACTERISTICS FOR REFERENCE 1 (LNA-mode)**($T_A = +25^\circ\text{C}$, $V_{CC} = V_{cont} = 3.3\text{ V}$, $Z_S = Z_L = 75\ \Omega$, unless otherwise specified)**

Parameter	Symbol	Test Conditions	Reference Value	Unit
Isolation 1	ISL1	$f = 40\text{ MHz}$, $P_{in} = -20\text{ dBm}$	20	dB
Isolation 2	ISL2	$f = 1\ 000\text{ MHz}$, $P_{in} = -20\text{ dBm}$	20	dB
Gain 1 dB Compression Output Power	$P_{O(1\text{ dB})}$	$f = 500\text{ MHz}$	+10	dBm

STANDARD CHARACTERISTICS FOR REFERENCE 2 (Bypass-mode)**($T_A = +25^\circ\text{C}$, $V_{CC} = 3.3\text{ V}$, $V_{cont} = 0\text{ V}$, $Z_S = Z_L = 75\ \Omega$, unless otherwise specified)**

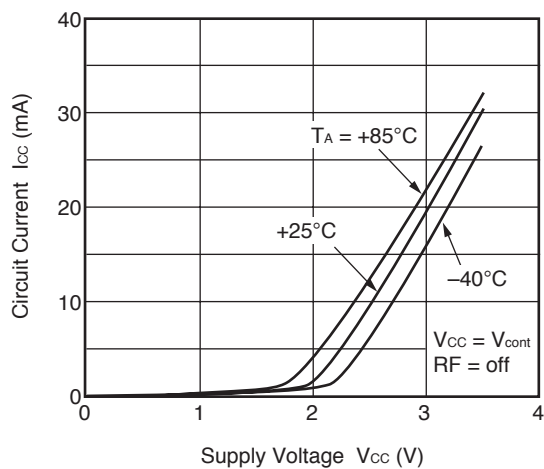
Parameter	Symbol	Test Conditions	Reference Value	Unit
Gain 1 dB Compression Output Power	$P_{O(1\text{ dB})}$	$f = 500\text{ MHz}$	Note	dBm

Note: The input-output power characteristic is not saturated up to +15 dBm of input power.

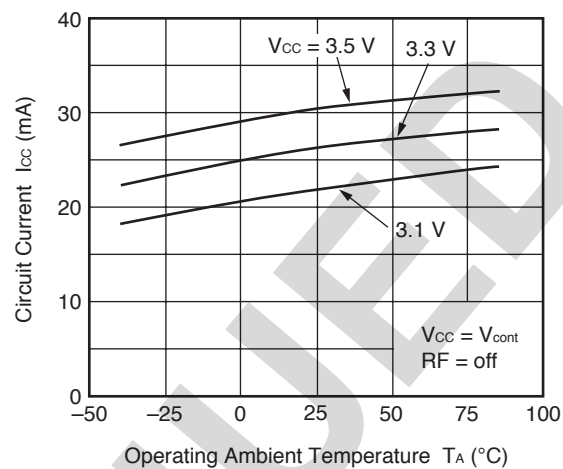
TEST CIRCUIT

TYPICAL CHARACTERISTICS 1 (DC Characteristics) **($T_A = +25^\circ\text{C}$, unless otherwise specified)**

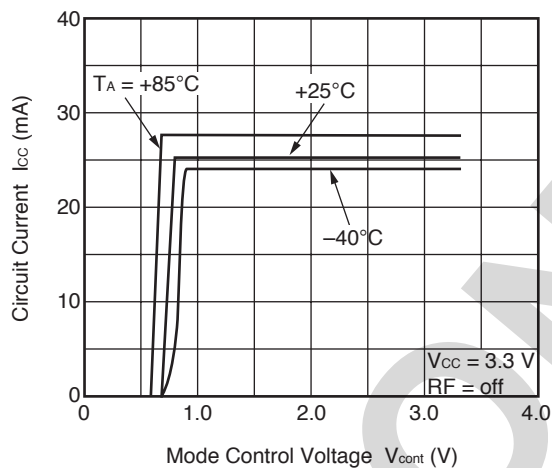
CIRCUIT CURRENT vs. SUPPLY VOLTAGE



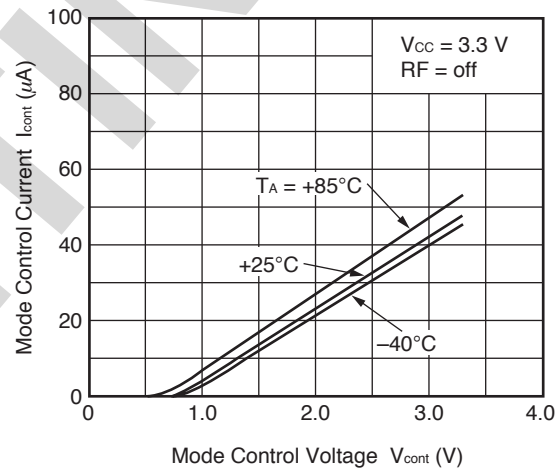
CIRCUIT CURRENT vs. OPERATING AMBIENT TEMPERATURE



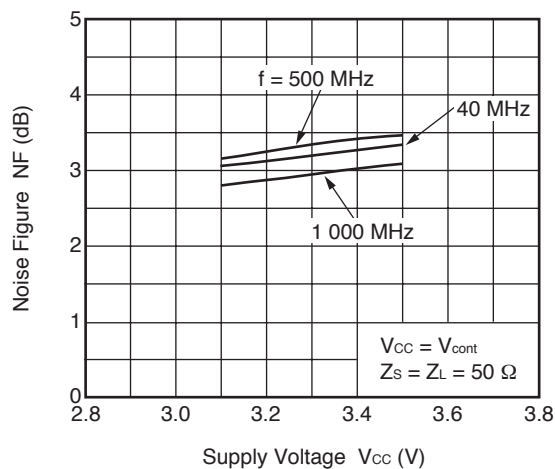
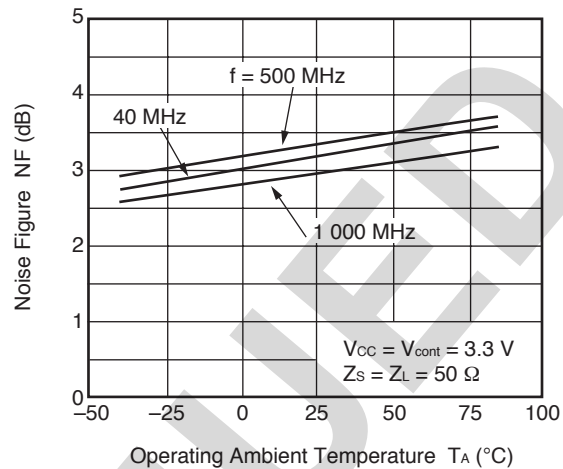
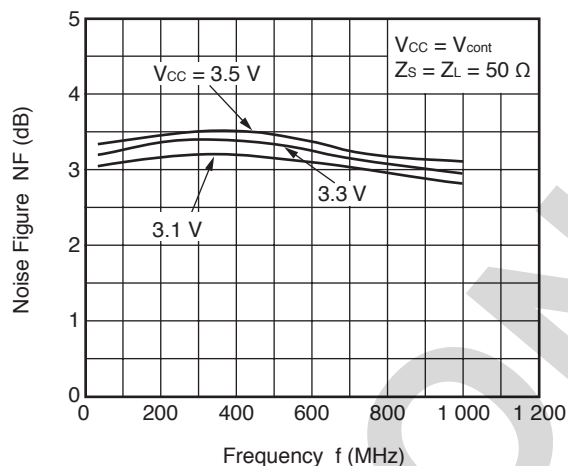
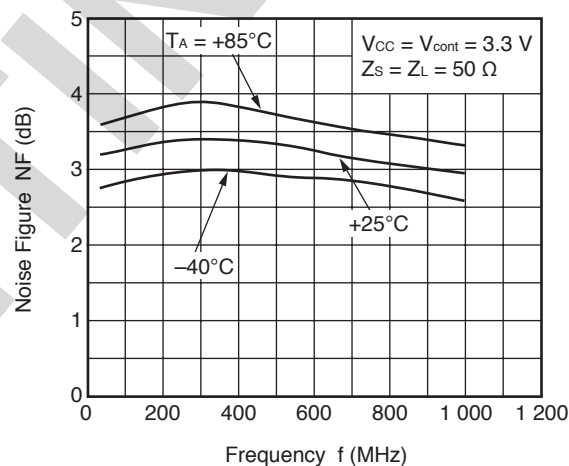
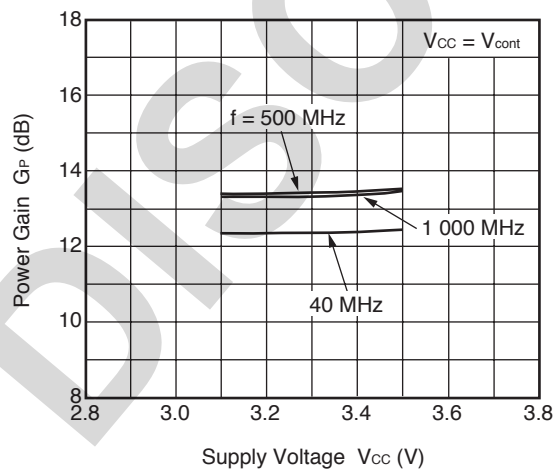
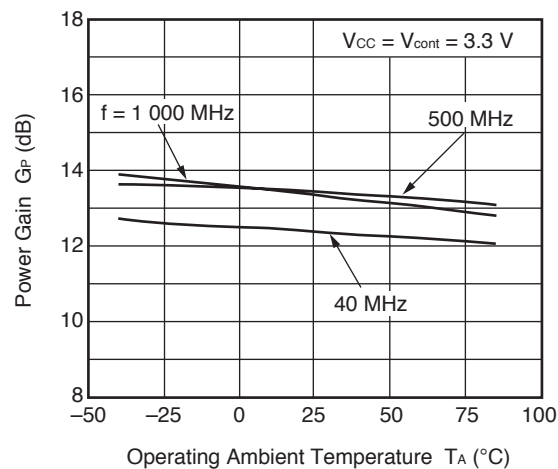
CIRCUIT CURRENT vs. MODE CONTROL VOLTAGE

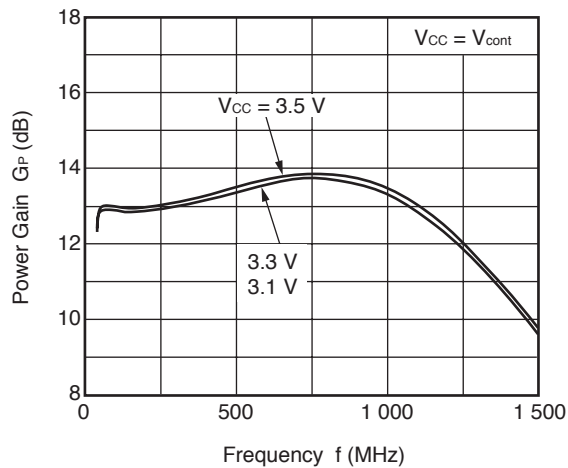
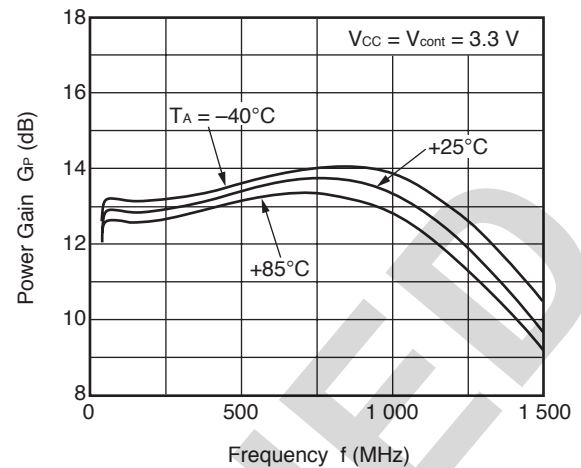
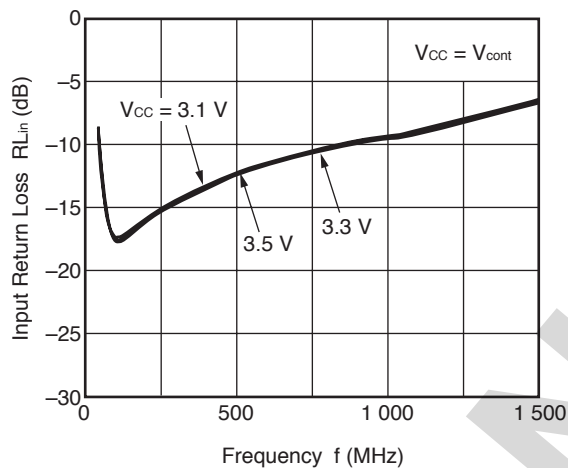
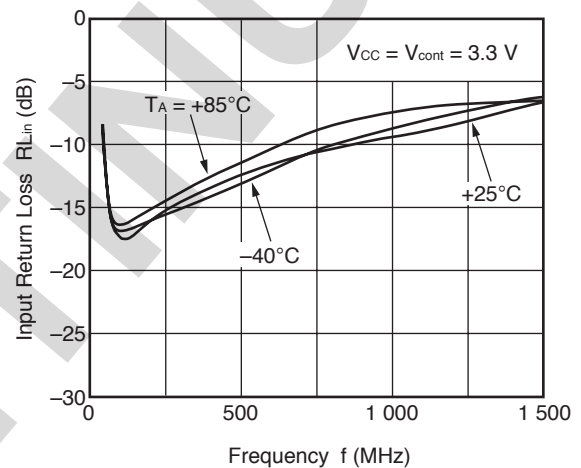
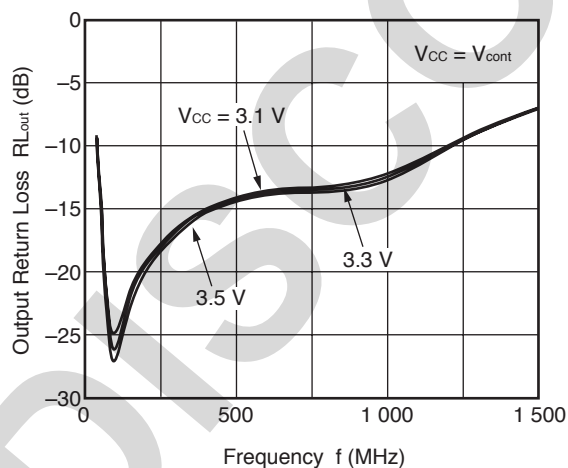
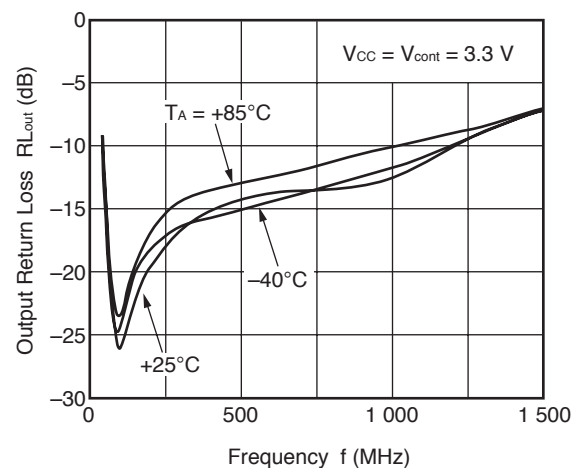


MODE CONTROL CURRENT vs. MODE CONTROL VOLTAGE

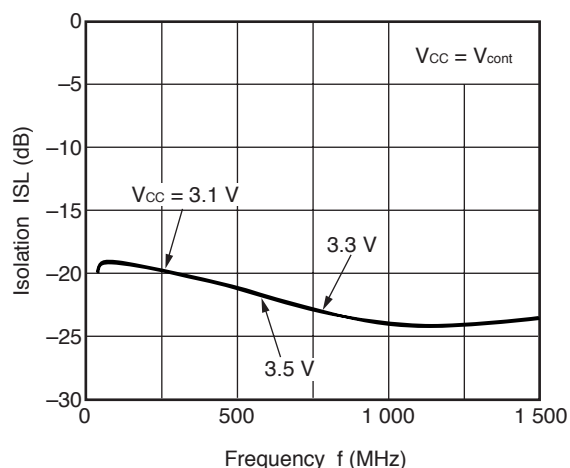
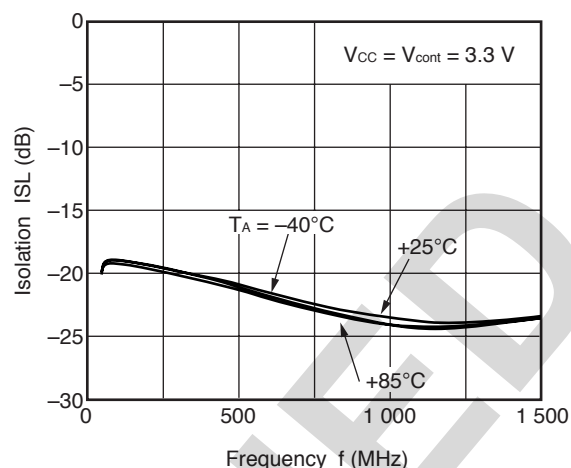
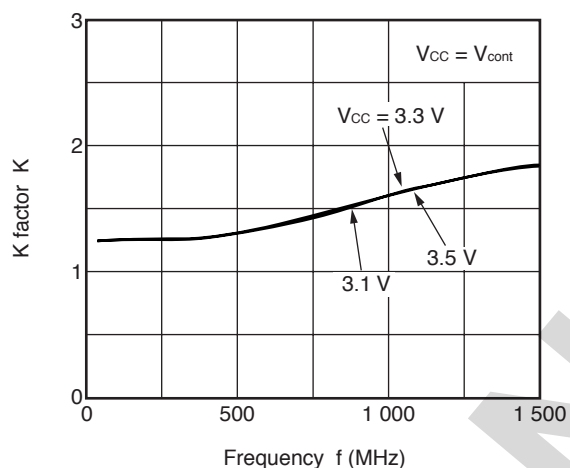
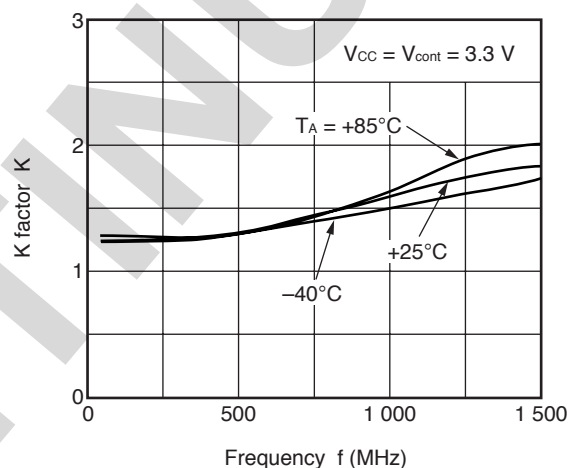
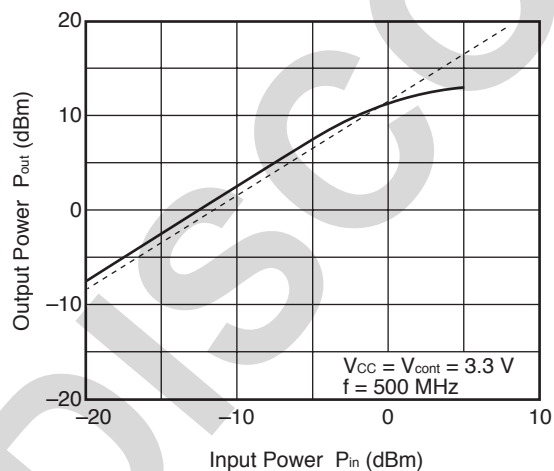
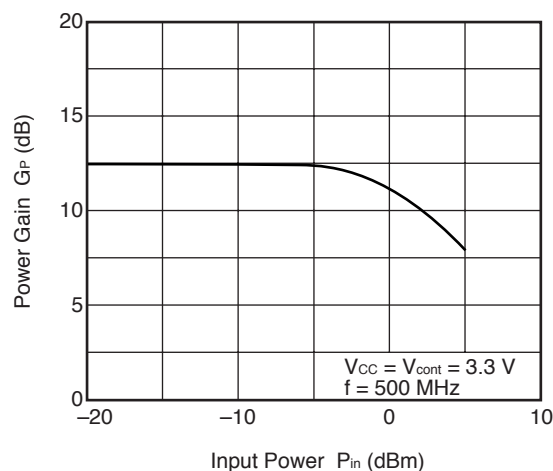


Remark The graphs indicate nominal characteristics.

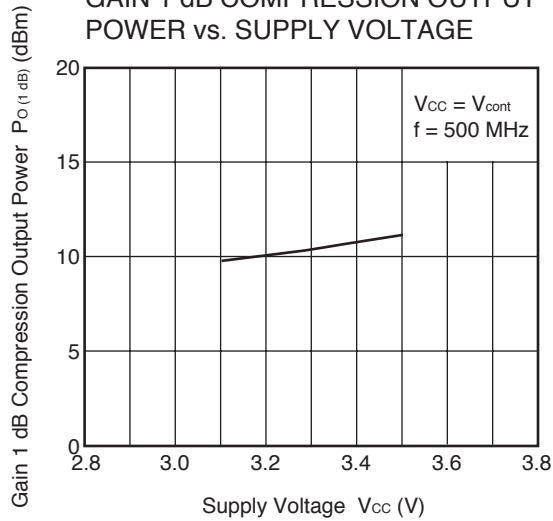
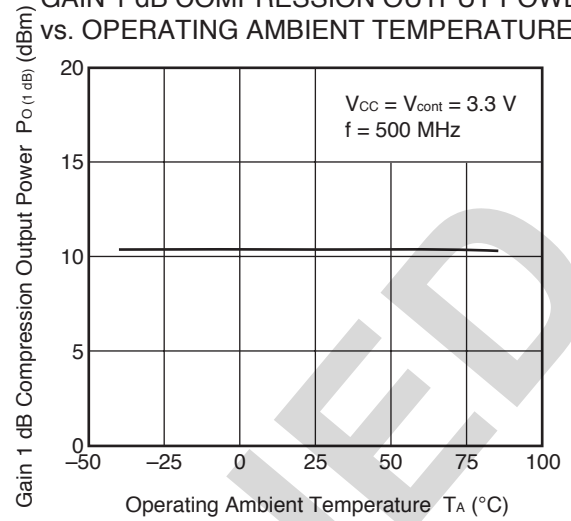
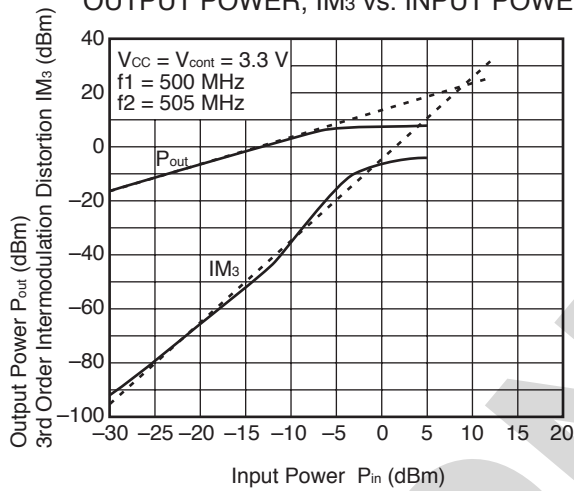
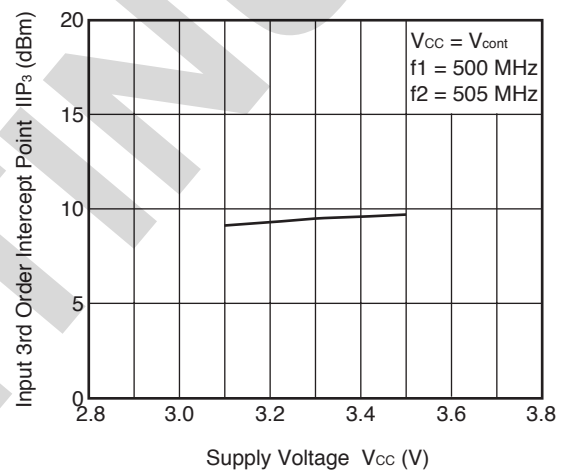
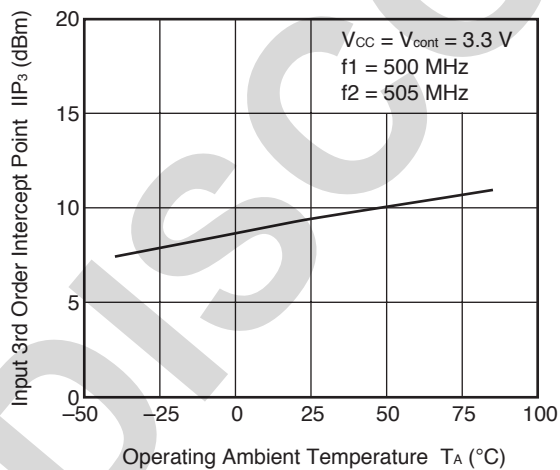
TYPICAL CHARACTERISTICS 2 (LNA-mode)**($T_A = +25^\circ\text{C}$, $Z_S = Z_L = 75\ \Omega$, unless otherwise specified)****NOISE FIGURE vs. SUPPLY VOLTAGE****NOISE FIGURE vs. OPERATING AMBIENT TEMPERATURE****NOISE FIGURE vs. FREQUENCY****NOISE FIGURE vs. FREQUENCY****POWER GAIN vs. SUPPLY VOLTAGE****POWER GAIN vs. OPERATING AMBIENT TEMPERATURE****Remark** The graphs indicate nominal characteristics.

POWER GAIN vs. FREQUENCY**POWER GAIN vs. FREQUENCY****INPUT RETURN LOSS vs. FREQUENCY****INPUT RETURN LOSS vs. FREQUENCY****OUTPUT RETURN LOSS vs. FREQUENCY****OUTPUT RETURN LOSS vs. FREQUENCY**

Remark The graphs indicate nominal characteristics.

ISOLATION vs. FREQUENCY**ISOLATION vs. FREQUENCY****K FACTOR vs. FREQUENCY****K FACTOR vs. FREQUENCY****OUTPUT POWER vs. INPUT POWER****POWER GAIN vs. INPUT POWER**

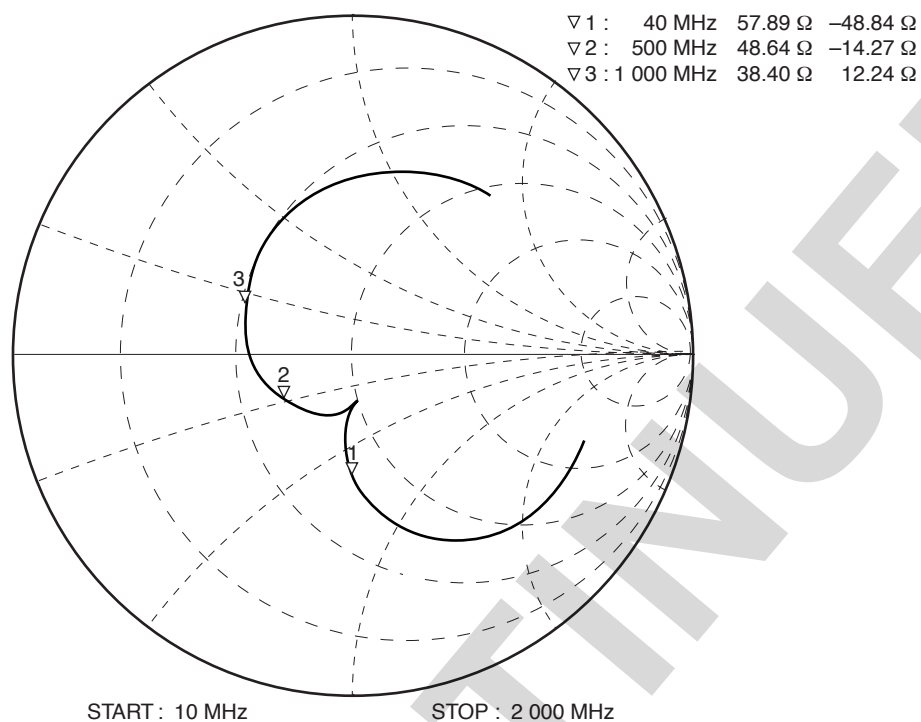
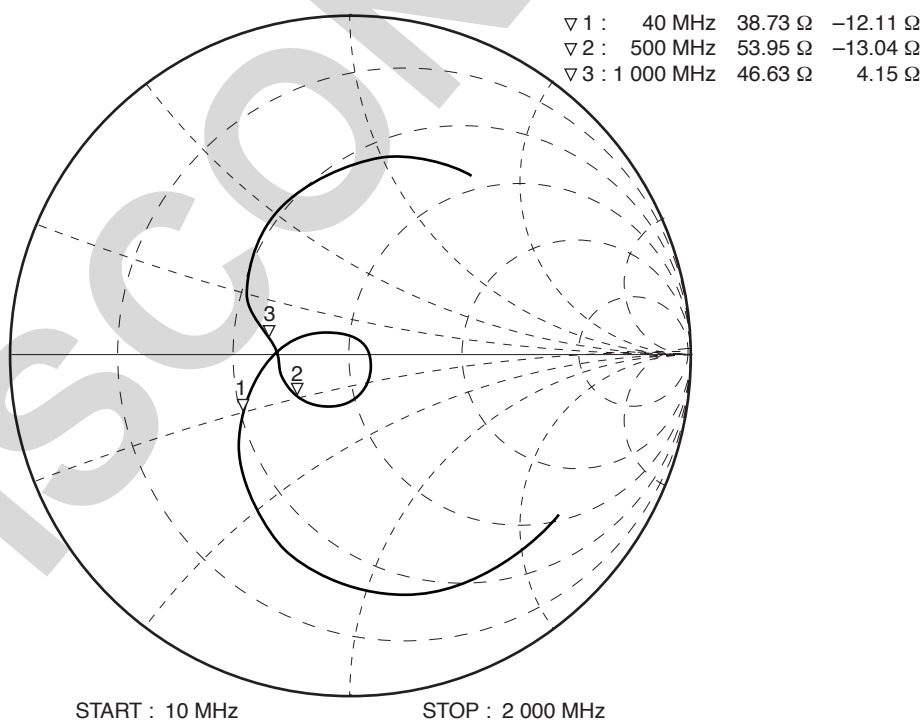
Remark The graphs indicate nominal characteristics.

GAIN 1 dB COMPRESSION OUTPUT POWER vs. SUPPLY VOLTAGE**GAIN 1 dB COMPRESSION OUTPUT POWER vs. OPERATING AMBIENT TEMPERATURE****OUTPUT POWER, IM_3 vs. INPUT POWER****INPUT 3RD ORDER INTERCEPT POINT vs. SUPPLY VOLTAGE****INPUT 3RD ORDER INTERCEPT POINT vs. OPERATING AMBIENT TEMPERATURE**

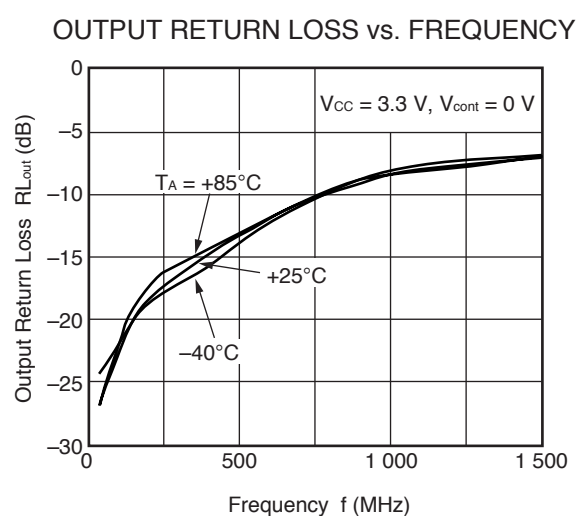
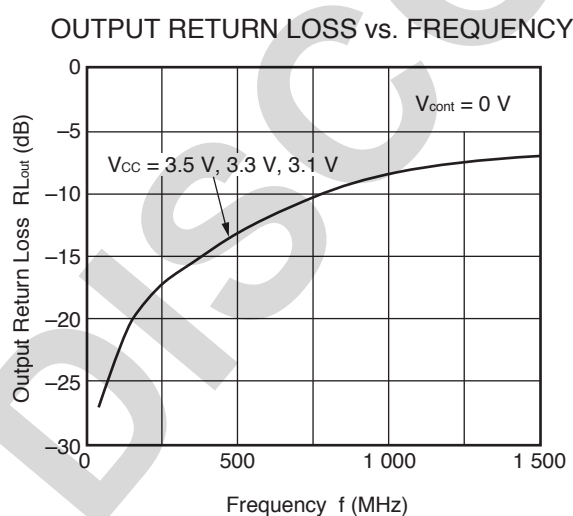
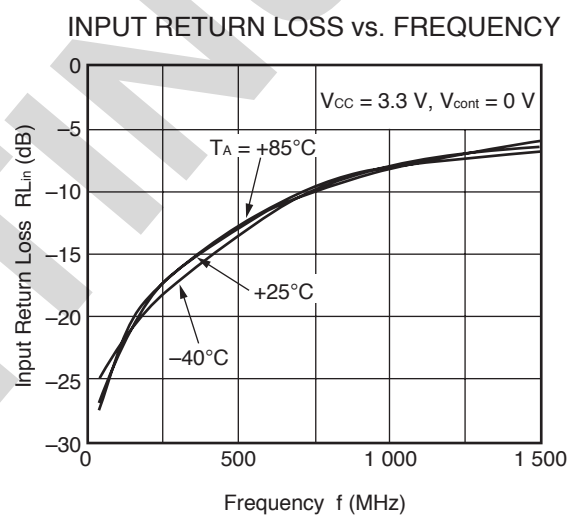
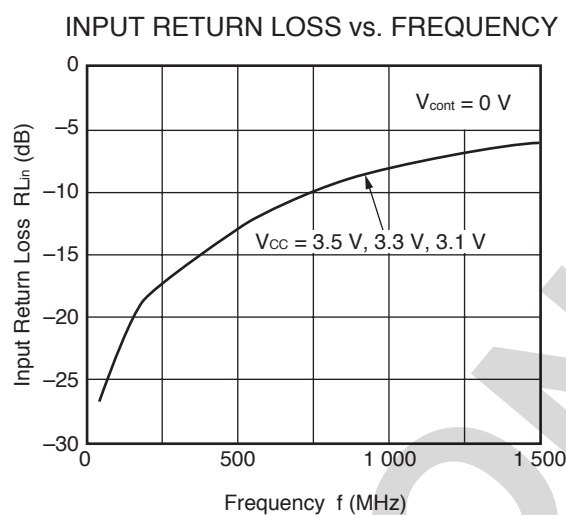
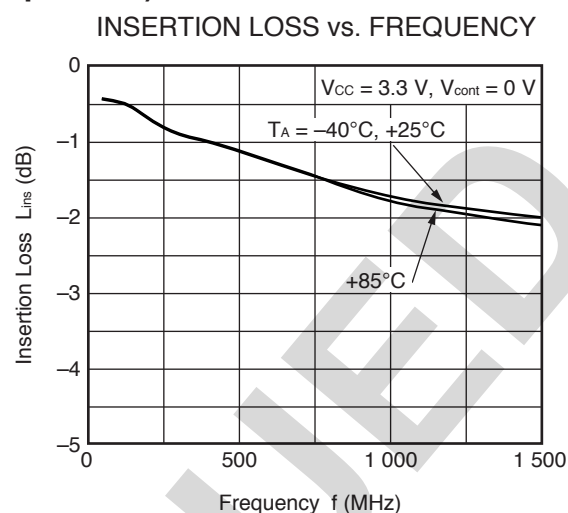
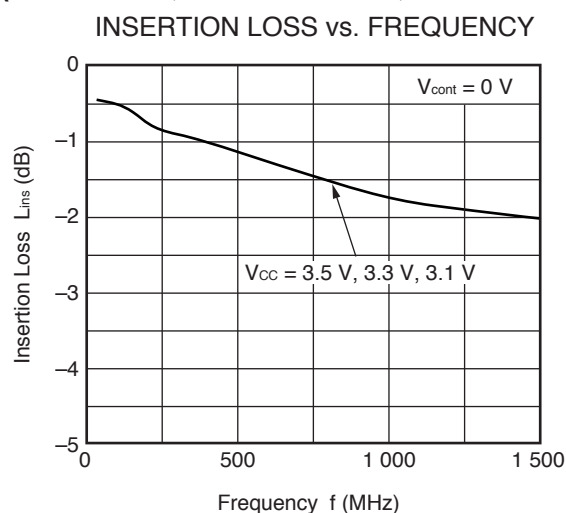
Remark The graphs indicate nominal characteristics.

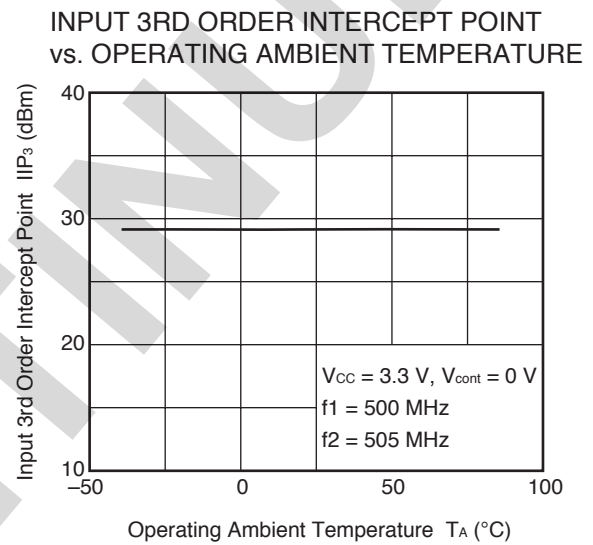
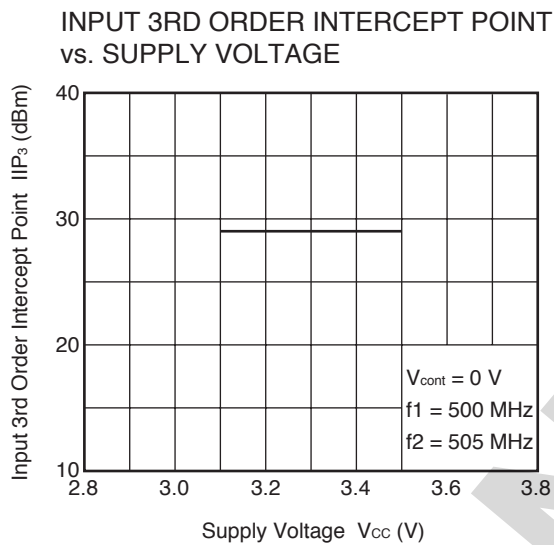
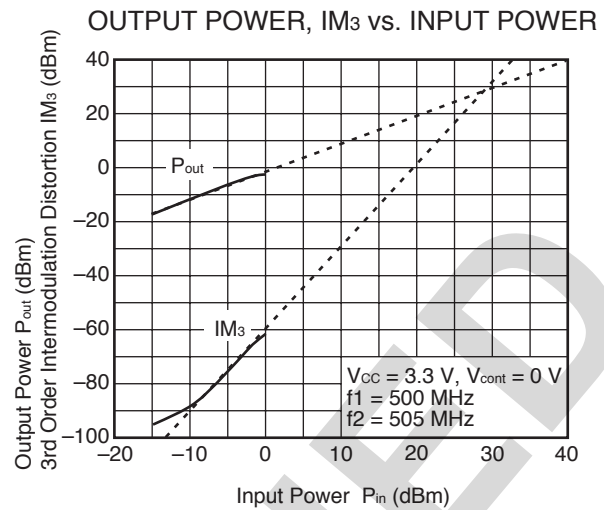
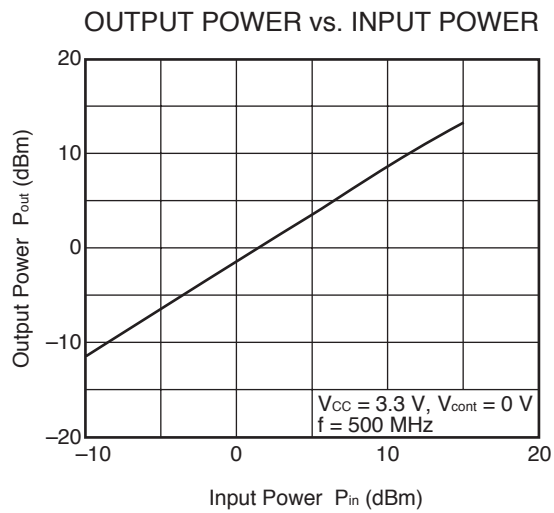
S-PARAMETERS 1 (LNA-mode)

($T_A = +25^\circ\text{C}$, $V_{CC} = V_{cont} = 3.3\text{ V}$, $Z_S = Z_L = 75\ \Omega$, monitored at connector on board)

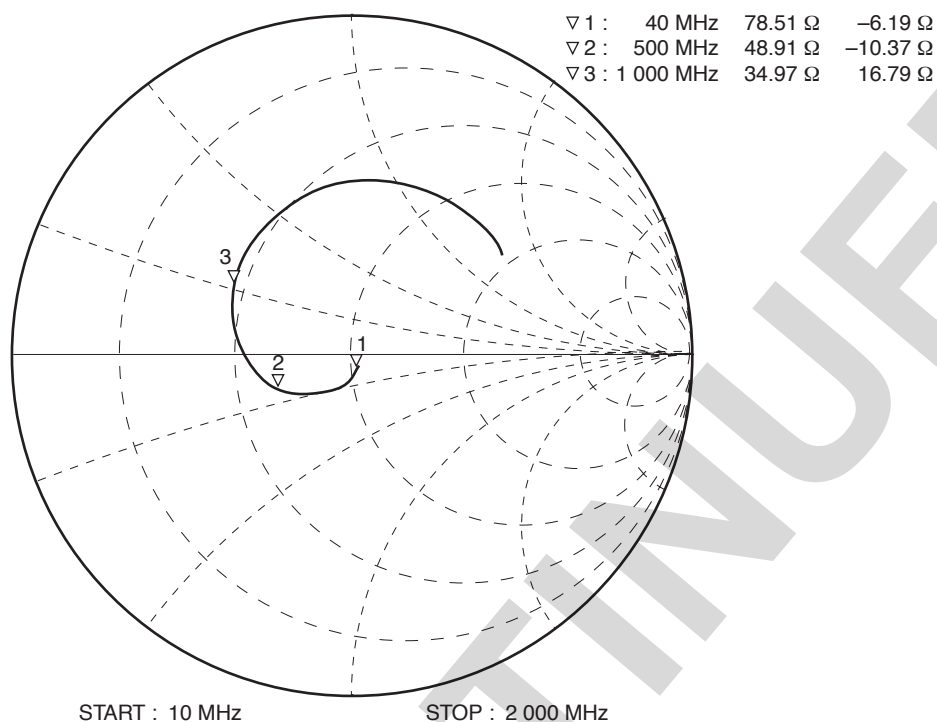
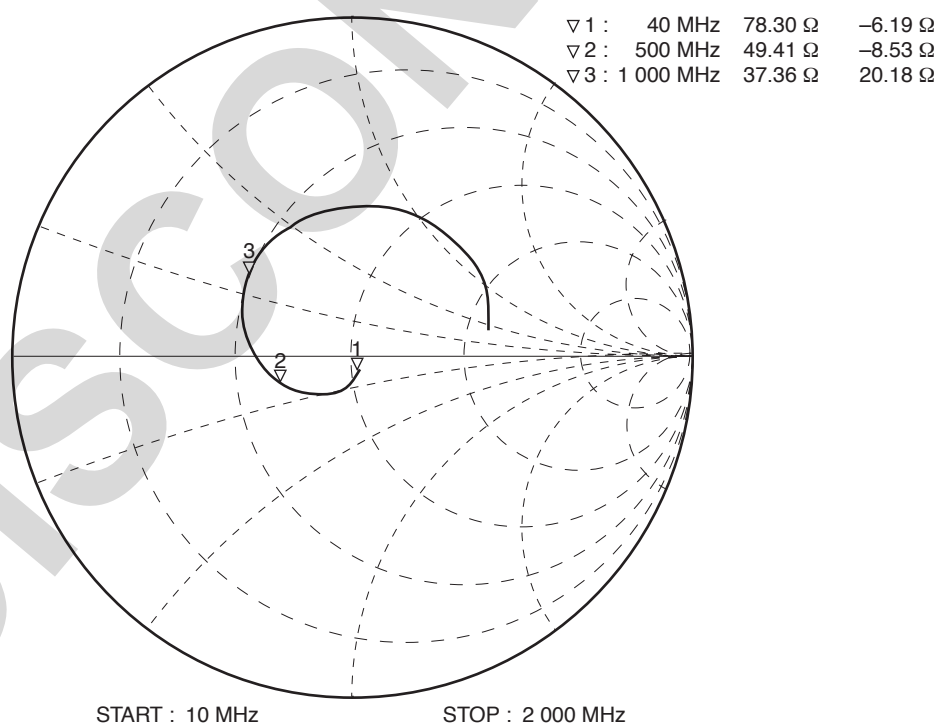
S₁₁-FREQUENCY**S₂₂-FREQUENCY**

Remark The graphs indicate nominal characteristics.

TYPICAL CHARACTERISTICS 3 (Bypass-mode)**($T_A = +25^\circ\text{C}$, $Z_S = Z_L = 75\ \Omega$, unless otherwise specified)****Remark** The graphs indicate nominal characteristics.

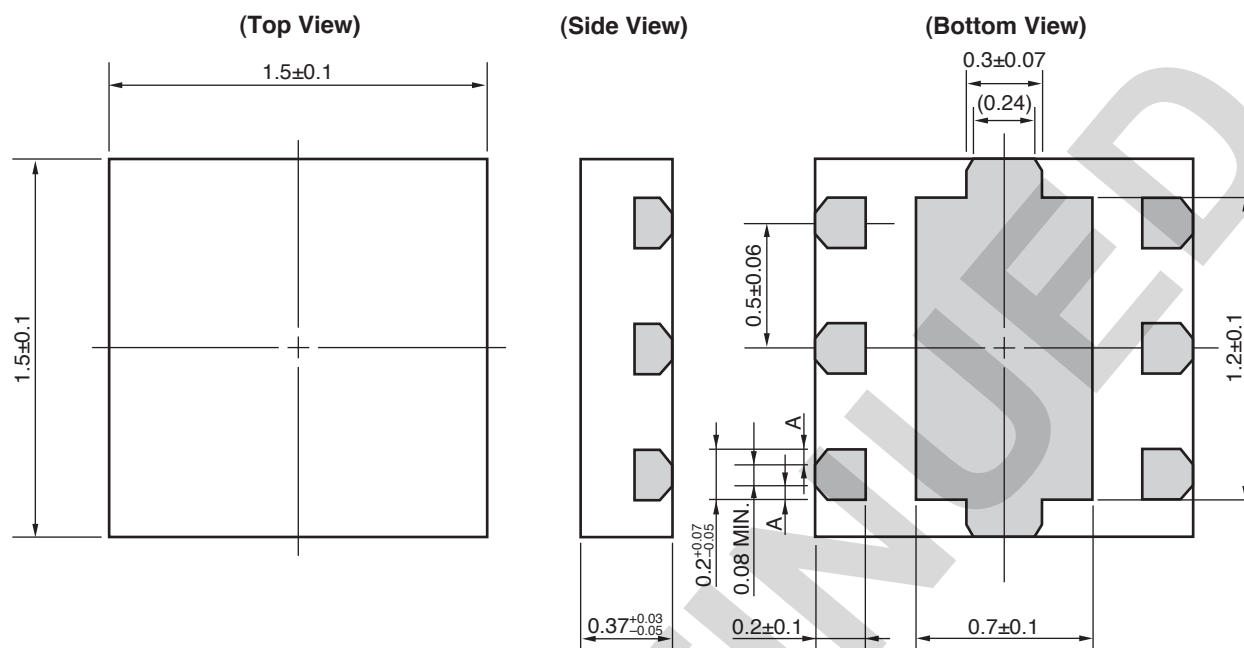


Remark The graphs indicate nominal characteristics.

S-PARAMETERS 2 (Bypass-mode)(T_A = +25°C, V_{CC} = 3.3 V, V_{cont} = 0 V, Z_S = Z_L = 75 Ω , monitored at connector on board)**S₁₁-FREQUENCY****S₂₂-FREQUENCY****Remark** The graphs indicate nominal characteristics.

PACKAGE DIMENSIONS

6-PIN PLASTIC TSON (T6N) (UNIT: mm)



Remark A>0

() : Reference value

NOTES ON CORRECT USE

- (1) Observe precautions for handling because of electro-static sensitive devices.
- (2) Form a ground pattern as widely as possible to minimize ground impedance (to prevent undesired oscillation).
- (3) All the ground terminals should be connected to the ground plane as close as possible.
- (4) The bypass capacitor should be attached to V_{CC} line.
- (5) Do not supply DC voltage to INPUT pin.

RECOMMENDED SOLDERING CONDITIONS

This product should be soldered and mounted under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your nearby sales office.

Soldering Method	Soldering Conditions	Condition Symbol
Infrared Reflow	Peak temperature (package surface temperature) : 260°C or below Time at peak temperature : 10 seconds or less Time at temperature of 220°C or higher : 60 seconds or less Preheating time at 120 to 180°C : 120±30 seconds Maximum number of reflow processes : 3 times Maximum chlorine content of rosin flux (% mass) : 0.2%(Wt.) or below	IR260
Partial Heating	Peak temperature (terminal temperature) : 350°C or below Soldering time (per side of device) : 3 seconds or less Maximum chlorine content of rosin flux (% mass) : 0.2%(Wt.) or below	HS350

CAUTION

Do not use different soldering methods together.

Revision History	μPD5756T6N Data Sheet
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Rev.	Date	Description	
		Page	Summary
1.00	Oct 04, 2011	—	First edition issued

DISCONTINUED